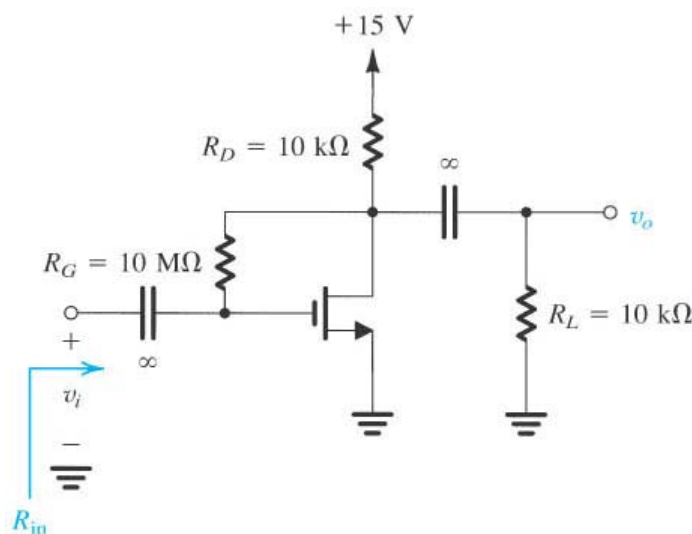


## Lecture 29: MOSFET Small-Signal Amplifier Examples.

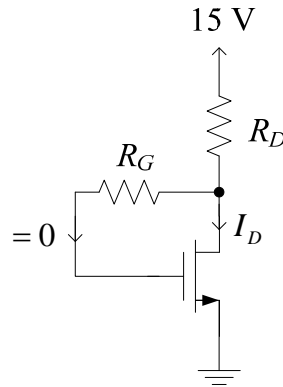
We will illustrate the analysis of small-signal MOSFET amplifiers through two examples in this lecture.

**Example N29.1** (text example 4.10). Determine  $A_v$  (neglecting the effects of  $R_G$ ),  $R_{in}$ , and  $R_{out}$  for the circuit below given that  $V_t = 1.5$  V,  $k_n' W/L = 0.25$  mA/V<sup>2</sup>, and  $V_A = 50$  V.



(Fig. 4.38a)

The first step is to determine the **DC operating point**. The DC equivalent circuit is:



Since  $V_{GD} = 0 < V_t$  the MOSFET is operating in the saturation mode if  $I_D \neq 0$ . Assuming operation in the saturation mode the DC drain current from (4.22) is

$$I_D = \frac{1}{2} k_n' \frac{W}{L} (V_{GS} - V_t)^2 (1 + \lambda V_{DS}) \quad (4.22)$$

Notice in the circuit that  $V_{GS} = V_{DS}$ , so we will eventually create a triatic equation in  $V_{GS}$  for  $I_D$ .

However, the last factor in (4.22) will be quite small for large  $V_A$  (small  $\lambda$ ). So, for simplicity we will neglect  $r_o$  giving

$$I_D \approx \frac{1}{2} k_n' \frac{W}{L} (V_{GS} - V_t)^2 \quad (4.20)$$

For this DC circuit

$$I_D = \frac{1}{2} \cdot 0.25 \times 10^{-3} (V_{GS} - 1.5)^2 = 1.25 \times 10^{-4} (V_{GS} - 1.5)^2$$

Notice in the circuit that  $V_{GS} = V_{DS}$  so that this last equation becomes

$$I_D = 0.125 (V_{DS} - 1.5)^2 \text{ mA} \quad (4.73), (1)$$

Also, by KVL

$$V_{DS} = 15 - R_D I_D = 15 - 10,000 I_D \quad (4.74), (2)$$

Substituting (2) into (1)

$$I_D = 1.25 \times 10^{-4} (15 - 10,000 I_D - 1.5)^2$$

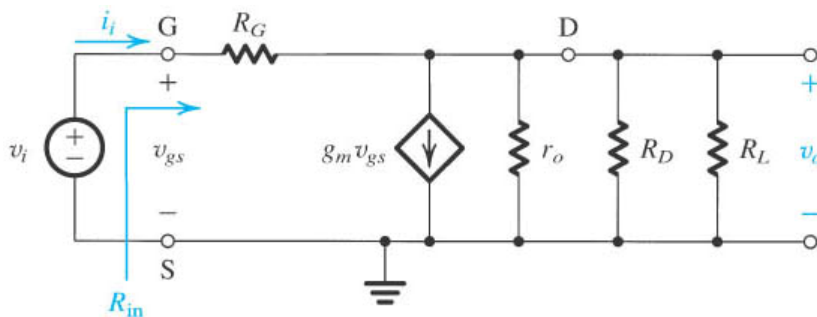
Solving this equation gives

$$I_D = 1.06 \text{ mA} \Rightarrow V_{DS} = 4.4 \text{ V} (= V_{GS})$$

or  $I_D = 1.72 \text{ mA} \Rightarrow V_{DS} = -2.2 \text{ V} (= V_{GS})$

This latter result is **not consistent** with the assumption of operation in the saturation mode since  $V_{GS} < V_t = 1.5 \text{ V}$ . So the **proper solution** for  $I_D$  is the first ( $I_D = 1.06 \text{ mA}$ ).

Next, we construct the small-signal equivalent circuit. We'll use the  $\pi$  small-signal model of the MOSFET with  $r_o$  included:



(Fig. 4.38b)

$$\checkmark g_m = k_n' \frac{W}{L} (V_{GS} - V_t) = 0.25 \times 10^{-3} (4.4 - 1.5) = 0.725 \text{ mS}$$

$$\checkmark r_o = \frac{V_A}{I_D} = \frac{50}{1.06 \text{ mA}} = 47.2 \text{ k}\Omega$$

Recall from the previous lecture that the proper  $I_D$  in the  $r_o$  calculation is that with  $\lambda = 0$ , which is what we ended up calculating earlier.

To compute the **small-signal voltage gain**, we start at the output (assuming  $R_G$  is extremely large  $R_G \gg r_o \parallel R_D \parallel R_L$ )

$$v_o \approx -g_m v_{gs} (r_o \parallel R_D \parallel R_L)$$

At the input notice that  $v_{gs} = v_i$ . Therefore

$$A_v = \frac{v_o}{v_i} \approx -g_m (r_o \parallel R_D \parallel R_L) = -g_m (4,521) = -3.28 \text{ V/V}$$

Notice that the assumption  $R_G \gg r_o \parallel R_D \parallel R_L$  is met and hugely exceeded since  $10 \text{ M}\Omega \gg 4,521 \Omega$ .

For the input resistance  $R_{in}$  calculation, we cannot set  $v_{gs} = 0$  – and subsequently open circuit the dependent current source – since this would artificially force  $R_{in} = 0$ . Rather, we need to **determine  $i_i$  as a function of  $v_i$**  and use this in the definition:

$$R_{in} \equiv \frac{v_i}{i_i}$$

The dependent current source will remain in these calculations.

Proceeding, at the input of the small-signal equivalent circuit shown above

$$i_i = \frac{v_i - v_o}{R_G} = \frac{v_i}{R_G} \left( 1 - \frac{v_o}{v_i} \right) = \frac{v_i}{R_G} (1 - A_v)$$

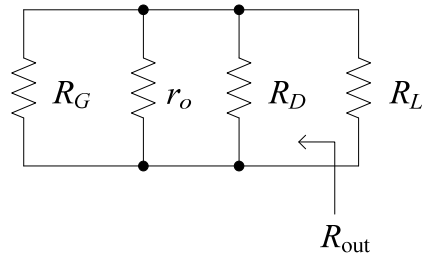
Therefore,

$$i_i = \frac{v_i}{R_G} (1 + 3.28)$$

Consequently, using this expression we find that

$$R_{in} = \frac{v_i}{i_i} = \frac{R_G}{4.28} = 2.34 \text{ M}\Omega$$

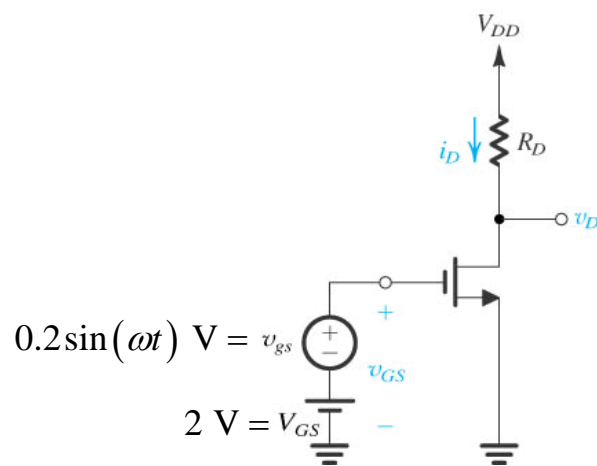
Lastly, to determine the output resistance, we can set  $v_{gs} = 0$  in the small-signal equivalent circuit above, which will open circuit the dependent current source leading to the equivalent circuit:



from which we see that

$$R_{\text{out}} = R_G \parallel r_o \parallel R_D = 8.24 \text{ k}\Omega$$

**Example N29.2** (text exercise 4.23). Determine the following quantities for the conceptual MOSFET small-signal amplifier of Fig. 4.34 given that  $V_{DD} = 5 \text{ V}$ ,  $R_D = 10 \text{ k}\Omega$ , and  $V_{GS} = 2 \text{ V}$ .



(Fig. 4.34)

The MOSFET characteristics are  $V_t = 1 \text{ V}$ ,  $k_n' = 20 \text{ }\mu\text{A/V}^2$ ,  $W/L = 20$ , and  $\lambda = 0$ .

- (a) Determine  $I_D$  and  $V_D$ . We see from the circuit that  $V_{GS} > V_t$ . Therefore, the MOSFET is operating in the saturation or triode mode. We'll **assume saturation**. In that case

$$I_D = \frac{1}{2} k_n' \frac{W}{L} (V_{GS} - V_t)^2 = \frac{1}{2} \cdot 20 \times 10^{-6} \cdot 20(2 - 1)^2 = \mathbf{0.2 \text{ mA}}$$

and 
$$V_D = V_{DD} - I_D R_D = \mathbf{3 \text{ V}}$$

Let's check if the MOSFET is operating in the saturation mode:

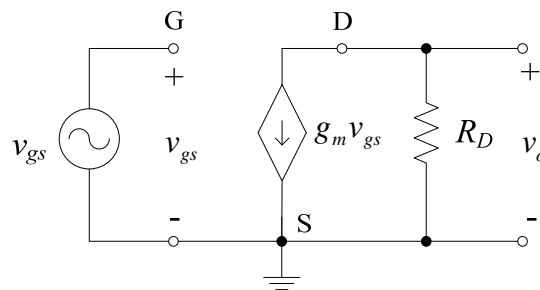
$$V_{GD} = 2 - 3 = -1 < V_t$$

Therefore, the MOSFET is **indeed saturated**, as assumed.

- (b) Determine  $g_m$ . Using (4.61)

$$g_m = k_n' \frac{W}{L} (V_{GS} - V_t) = 20 \times 10^{-6} \cdot 20 \cdot (2 - 1) = \mathbf{4.0 \text{ mS}}$$

- (c) Determine the voltage gain  $A_v$ . We begin by first constructing the **small-signal equivalent circuit**



Directly from this circuit,

$$v_o = -g_m v_{gs} R_D$$

so  $A_v = \frac{v_o}{v_{gs}} = -g_m R_D = -0.4 \times 10^{-3} \cdot 10 \times 10^3 = -4 \text{ V/V}$

(d) If  $v_{gs} = 0.2 \sin(\omega t) \text{ V}$ , find  $v_d$  and the max/min  $v_D$ .

$$A_v \equiv \frac{v_o}{v_{gs}} \Rightarrow v_d = A_v v_{gs} = -4 \cdot 0.2 \sin(\omega t)$$

Therefore,  $v_d = -0.8 \sin(\omega t) \text{ V}$

Hence,  $v_{D|_{\max}} = V_D + V_d = 3 + 0.8 = 3.8 \text{ V}$

while  $v_{D|_{\min}} = V_D - V_d = 3 - 0.8 = 2.2 \text{ V}$

(e) Determine the **second harmonic distortion**. From (4.57) or (6) in the previous lecture notes, the drain current is given as

$$i_D = I_D + k_n' \frac{W}{L} (V_{GS} - V_t) v_{gs} + \frac{1}{2} k_n' \frac{W}{L} v_{gs}^2$$

$$\begin{aligned} \text{or } i_D &= I_D + 20 \times 10^{-6} \cdot 20(2-1) v_{gs} + \frac{1}{2} \cdot 20 \times 10^{-6} \cdot 20 v_{gs}^2 \\ &= I_D + 0.4 \times 10^{-3} v_{gs} + 0.2 \times 10^{-3} v_{gs}^2 \end{aligned}$$

Substituting  $v_{gs} = 0.2 \sin(\omega t)$  into this equation gives

$$i_D = I_D + 80 \times 10^{-6} \sin(\omega t) + 8 \times 10^{-6} \sin^2(\omega t)$$

Using the trigonometry identity

$$\sin^2(\omega t) = 1/2 - 1/2 \cos(2\omega t)$$

this last expression becomes

$$i_D = 200 + 80 \sin(\omega t) + 4 - 4 \cos(2\omega t) \text{ } \mu\text{A}$$

or  $i_D = 204 + 80 \sin(\omega t) - 4 \cos(2\omega t) \text{ } \mu\text{A}$

The first term in  $i_D$  is  $I_D$ , the DC current. We see that there is a slight shift upward in value by  $4 \mu\text{A}$ .

The third term in  $i_D$  is the second harmonic term because it varies with time at twice the frequency of the input signal. The second harmonic distortion is

$$\frac{4}{80} \times 100\% = 5\%$$